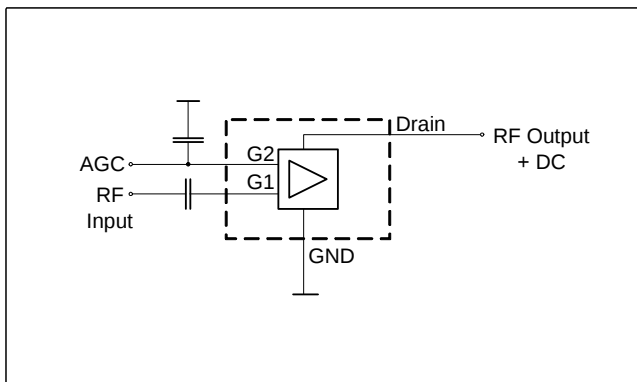
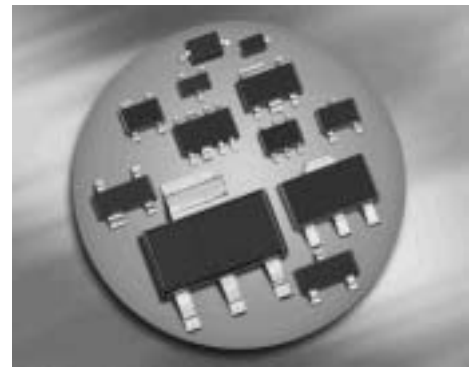


## Silicon N-Channel MOSFET Tetrode

- For low noise, high gain controlled input stages up to 1 GHz
- Operating voltage 5 V
- Integrated biasing network
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101



**ESD (Electrostatic discharge) sensitive device, observe handling precaution!**

| Type     | Package | Pin Configuration |     |      |      |   |   | Marking |
|----------|---------|-------------------|-----|------|------|---|---|---------|
| BF1005S  | SOT143  | 1=S               | 2=D | 3=G2 | 4=G1 | - | - | NZs     |
| BF1005SR | SOT143R | 1=D               | 2=S | 3=G1 | 4=G2 | - | - | NZs     |

### Maximum Ratings

| Parameter                                              | Symbol           | Value       | Unit             |
|--------------------------------------------------------|------------------|-------------|------------------|
| Drain-source voltage                                   | $V_{DS}$         | 8           | V                |
| Continuous drain current                               | $I_D$            | 25          | mA               |
| Gate 1/ gate 2-source current                          | $\pm I_{G1/2SM}$ | 10          |                  |
| Gate 1 (external biasing)                              | $+V_{G1SE}$      | 3           | V                |
| Total power dissipation<br>$T_S \leq 76^\circ\text{C}$ | $P_{tot}$        | 200         | mW               |
| Storage temperature                                    | $T_{stg}$        | -55 ... 150 | $^\circ\text{C}$ |
| Channel temperature                                    | $T_{ch}$         | 150         |                  |

<sup>1)</sup>Pb-containing package may be available upon special request

### Note:

**It is not recommended to apply external DC-voltage on Gate 1 in active mode.**

**Thermal Resistance**

| Parameter                               | Symbol      | Value      | Unit |
|-----------------------------------------|-------------|------------|------|
| Channel - soldering point <sup>1)</sup> | $R_{thchs}$ | $\leq 370$ | K/W  |

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

| Parameter | Symbol | Values |      |      | Unit |
|-----------|--------|--------|------|------|------|
|           |        | min.   | typ. | max. |      |

**DC Characteristics**

|                                                                                                |                    |    |     |     |               |
|------------------------------------------------------------------------------------------------|--------------------|----|-----|-----|---------------|
| Drain-source breakdown voltage<br>$I_D = 650 \mu\text{A}$ , $V_{G1S} = 0$ , $V_{G2S} = 0$      | $V_{(BR)DS}$       | 12 | -   | -   | V             |
| Gate1-source breakdown voltage<br>$+I_{G1S} = 10 \text{ mA}$ , $V_{G2S} = 0$ , $V_{DS} = 0$    | $+V_{(BR)G1SS}$    | 8  | -   | 12  |               |
| Gate2 source breakdown voltage<br>$\pm I_{G2S} = 10 \text{ mA}$ , $V_{G1S} = 0$ , $V_{DS} = 0$ | $\pm V_{(BR)G2SS}$ | 8  | -   | 13  |               |
| Gate1-source leakage current<br>$V_{G1S} = 6 \text{ V}$ , $V_{G2S} = 0$                        | $+I_{G1SS}$        | -  | 100 | -   | $\mu\text{A}$ |
| Gate 2 source leakage current<br>$\pm V_{G2S} = 8 \text{ V}$ , $V_{G1S} = 0$ , $V_{DS} = 0$    | $\pm I_{G2SS}$     | -  | -   | 50  | nA            |
| Drain current<br>$V_{DS} = 5 \text{ V}$ , $V_{G1S} = 0$ , $V_{G2S} = 4 \text{ V}$              | $I_{DSS}$          | -  | -   | 800 | $\mu\text{A}$ |
| Operating current (selfbiased)<br>$V_{DS} = 5 \text{ V}$ , $V_{G2S} = 4 \text{ V}$             | $I_{DSO}$          | 8  | 13  | 16  | mA            |
| Gate2-source pinch-off voltage<br>$V_{DS} = 5 \text{ V}$ , $I_D = 100 \mu\text{A}$             | $V_{G2S(p)}$       | -  | 1   | -   | V             |

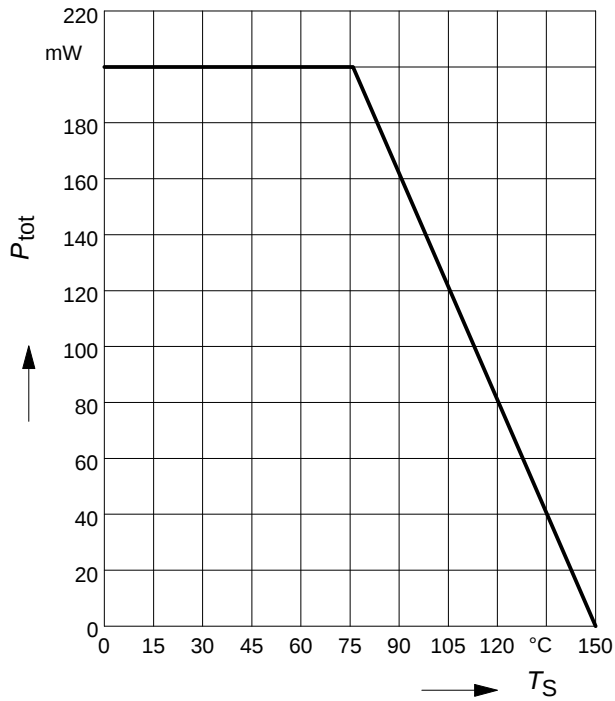
<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

| Parameter                                                                                                    | Symbol       | Values |      |      | Unit |
|--------------------------------------------------------------------------------------------------------------|--------------|--------|------|------|------|
|                                                                                                              |              | min.   | typ. | max. |      |
| AC Characteristics (verified by random sampling)                                                             |              |        |      |      |      |
| Forward transconductance<br>$V_{DS} = 5\text{ V}$ , $V_{G2S} = 4.5\text{ V}$                                 | $g_{fs}$     | 26     | 30   | -    | mS   |
| Gate1 input capacitance<br>$V_{DS} = 5\text{ V}$ , $V_{G2S} = 4\text{ V}$ , $f = 1\text{ MHz}$               | $C_{g1ss}$   | -      | 2.4  | 2.7  | pF   |
| Output capacitance<br>$V_{DS} = 5\text{ V}$ , $V_{G2S} = 4\text{ V}$ , $f = 100\text{ MHz}$                  | $C_{dss}$    | -      | 1.3  | -    |      |
| Power gain (self biased)<br>$V_{DS} = 5\text{ V}$ , $V_{G2S} = 4\text{ V}$ , $f = 800\text{ MHz}$            | $G_p$        | 20     | 22   | -    | dB   |
| Noise figure<br>$V_{DS} = 5\text{ V}$ , $V_{G2S} = 4\text{ V}$ , $f = 800\text{ MHz}$                        | $F$          | -      | 1.6  | 2.1  | dB   |
| Gain control range<br>$V_{DS} = 5\text{ V}$ , $V_{G2S} = 4\text{ V} \dots 0\text{ V}$ , $f = 800\text{ MHz}$ | $\Delta G_p$ | 40     | 50   | -    |      |

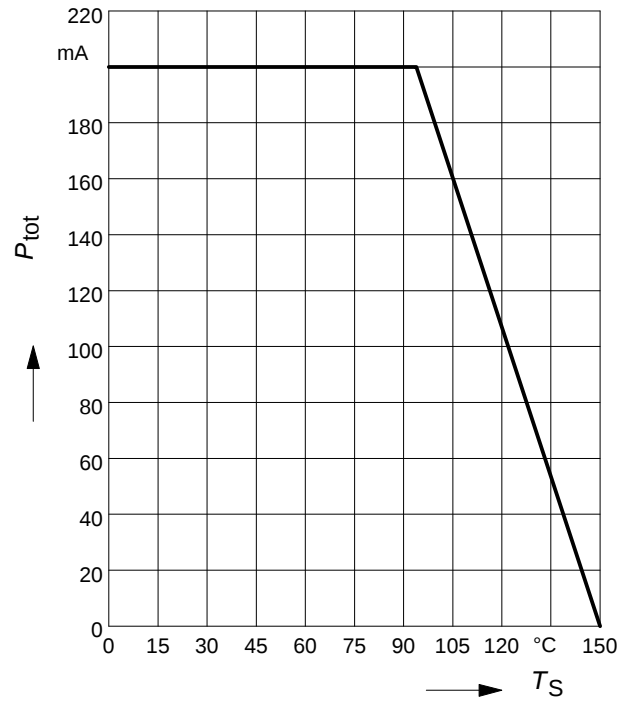
**Total power dissipation  $P_{\text{tot}} = f(T_S)$**

BF1005S, BF1005SR

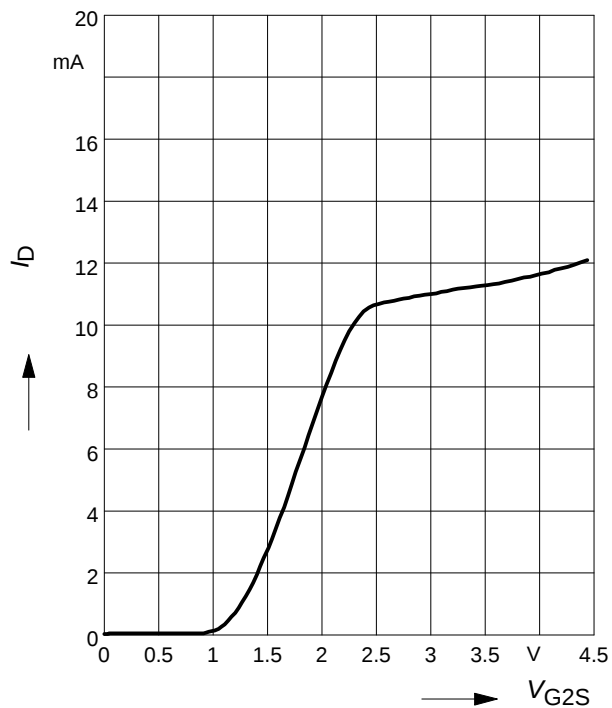


**Total power dissipation  $P_{\text{tot}} = f(T_S)$**

BF1005SW

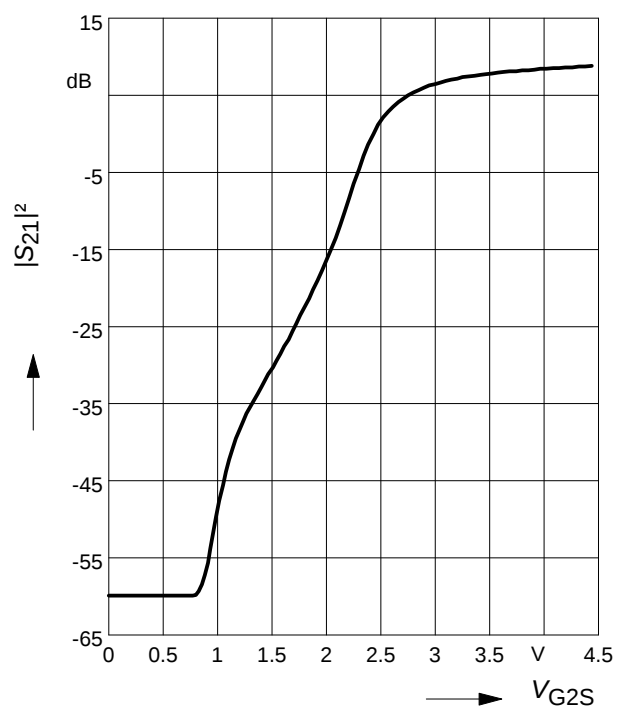


**Drain current  $I_D = f(V_{G2S})$**



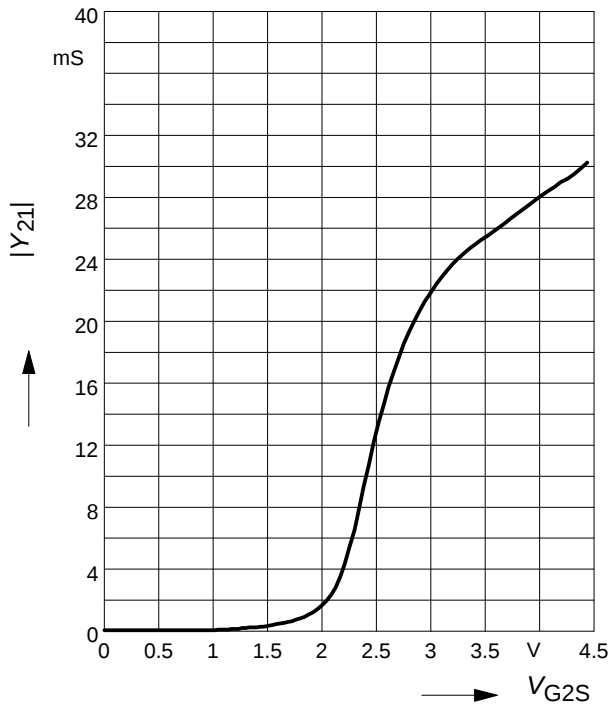
**Insertion power gain**

$|S_{21}|^2 = f(V_{G2S})$

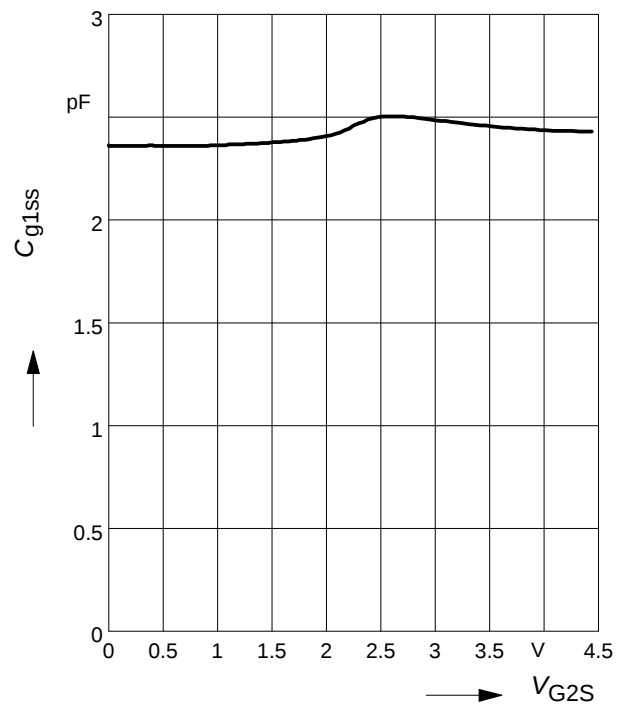


**Forward transfer admittance**

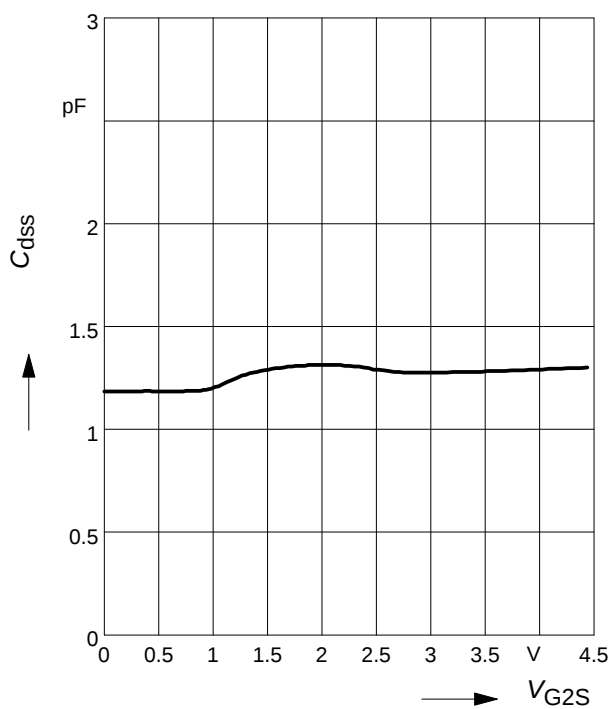
$$|Y_{21}| = f(V_{G2S})$$


**Gate 1 input capacitance  $C_{g1ss} = f(V_{G2S})$** 

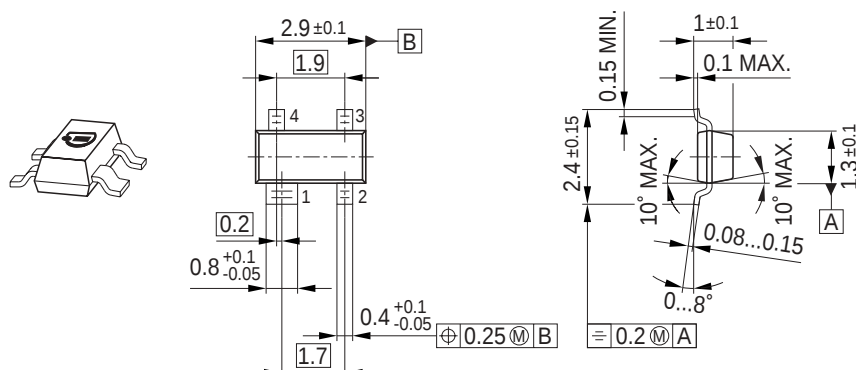
$$f = 200\text{MHz}$$


**Output capacitance  $C_{dss} = f(V_{G2S})$** 

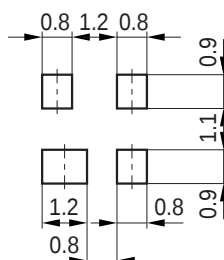
$$f = 200\text{MHz}$$



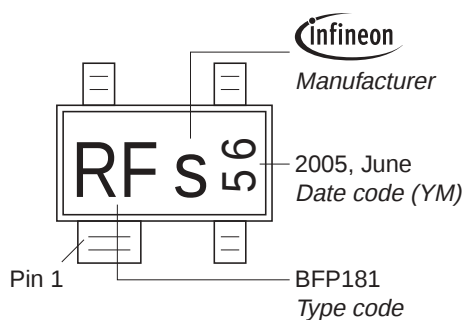
## Package Outline



## Foot Print

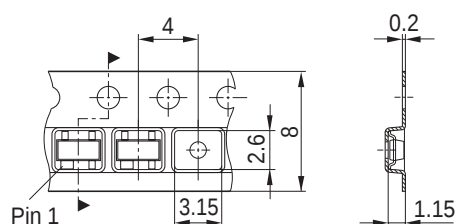


## Marking Layout (Example)

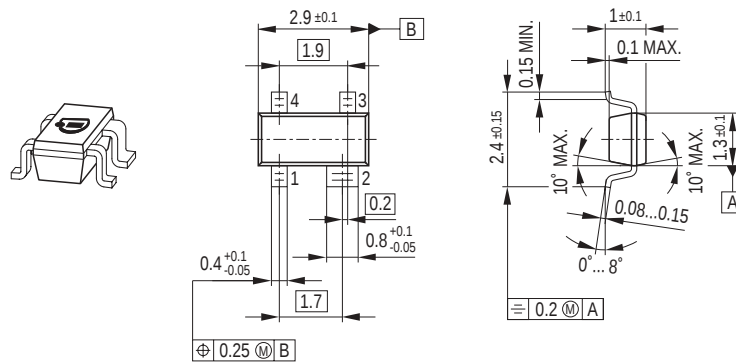


## Standard Packing

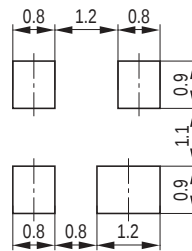
Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø330 mm = 10.000 Pieces/Reel



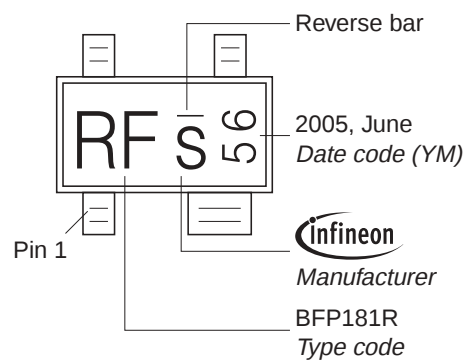
## Package Outline



## Foot Print

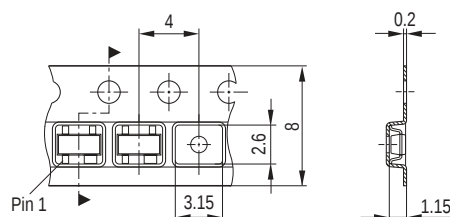


## Marking Layout (Example)



## Standard Packing

Reel  $\varnothing 180$  mm = 3.000 Pieces/Reel  
 Reel  $\varnothing 330$  mm = 10.000 Pieces/Reel



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